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P-Channel 60 V (D-S) MOSFET

PRODUCT SUMMARY					
V _{DS} (V)	$R_{DS(on)}\left(\Omega\right)$	I _D (A)			
- 60	0.045 at V _{GS} = - 10 V	- 40 ^d			
- 60	0.054 at V _{GS} = - 4.5 V	- 40 ^d			

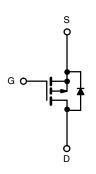
FEATURES

- TrenchFET® Power MOSFET
- Material categorization:



APPLICATIONS

Load Switch



P-Channel MOSFET

TO-252					
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ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C, unless otherwise noted)					
Parameter	Symbol	Limit	Unit		
Drain-Source Voltage		V _{DS}	- 60	V	
Gate-Source Voltage		V _{GS}	± 20]	
Continuous Drain Current (T _J = 175 °C)	T _C = 25 °C	l _D	- 40 ^d		
Continuous Brain Current (1) = 175 O)	T _C = 125 °C	טי	- 27.5	A	
Pulsed Drain Current	I _{DM}	- 110	A		
Avalanche Current	I _{AS}	- 30			
Single Pulse Avalanche Energy ^a	L = 0.1 mH	E _{AS}	125	mJ	
Power Dissipation	T _C = 25 °C	P _D	113 ^c	- W	
rower Dissipation	T _A = 25 °C] 'D	2.5 ^{b, c}		
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150	°C	

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Junction-to-Ambient ^b	t ≤ 10 s	- R _{thJA}	15	18	°C/W	
Junction-to-Ambient	Steady State		40	50		
Junction-to-Case		R_{thJC}	0.82	1.1		

Notes:

- a. Duty cycle \leq 1 %.
- b. When mounted on 1" square PCB (FR-4 material).
- c. See SOA curve for voltage derating.
- d. Package limited.



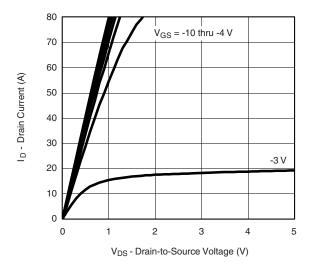
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static	•						
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_{D} = -250 \mu\text{A}$	- 60			V	
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	- 1		- 3	V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
		V _{DS} = - 60 V, V _{GS} = 0 V			- 1		
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = - 60 V, V _{GS} = 0 V, T _J = 125 °C			- 50	μΑ	
		V _{DS} = - 60 V, V _{GS} = 0 V, T _J = 150 °C			- 100		
On-State Drain Current ^a	I _{D(on)}	V _{DS} = - 5 V, V _{GS} = - 10 V	- 50			Α	
		V _{GS} = - 10 V, I _D = - 5 A		0.045	0.050		
	D	V _{GS} = - 10 V, I _D = - 10 A, T _J = 125 °C			0.060	0	
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = - 10 V, I _D = - 10 A, T _J = 150 °C			0.073	Ω	
		V _{GS} = - 4.5 V, I _D = - 5 A		0.054	0.060		
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 15 V, I _D = - 17 A		61		S	
Dynamic ^b	•				•		
Input Capacitance	C _{iss}			4950			
Output Capacitance	C _{oss}	$V_{GS} = 0 \text{ V}, V_{DS} = -25 \text{ V}, f = 1 \text{ MHz}$		480		pF	
Reverse Transfer Capacitance	C _{rss}			405			
Total Gate Charge ^c	Q_g			110	165		
Gate-Source Charge ^c	Q _{gs}	$V_{DS} = -30 \text{ V}, V_{GS} = -10 \text{ V}, I_{D} = -40 \text{ A}$		19		nC	
Gate-Drain Charge ^c	Q_{gd}			28			
Turn-On Delay Time ^c	t _{d(on)}			15	23		
Rise Time ^c	t _r	$V_{DD} = -30 \text{ V}, R_{L} = 0.6 \Omega$		70	105		
Turn-Off Delay Time ^c	t _{d(off)}	$I_D \cong -40 \text{ A}, V_{GEN} = -10 \text{ V}, R_G = 6$		175	260	ns	
Fall Time ^c	t _f	Ω		175	260		
Source-Drain Diode Ratings and Cha	aracteristics -	Γ _C = 25 °C ^b					
Continuous Current	I _S				- 40	٨	
Pulsed Current	I _{SM}				- 80	Α	
Forward Voltage ^a	V _{SD}	I _F = - 40 A, V _{GS} = 0 V		- 1	- 1.6	V	
Reverse Recovery Time	t _{rr}	I _F = - 40 A, dI/dt = 100 A/μs		45	70	ns	

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %. b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

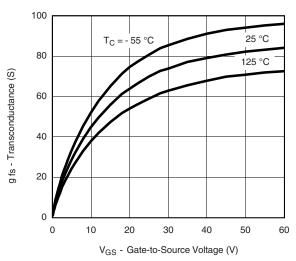
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



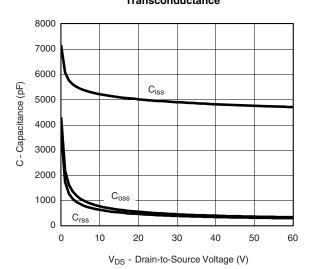
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



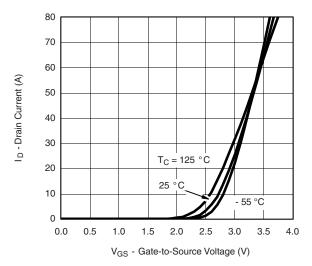
Output Characteristics



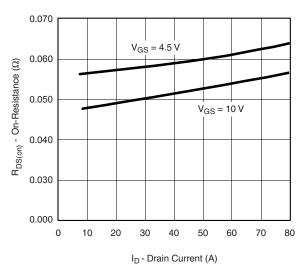
Transconductance



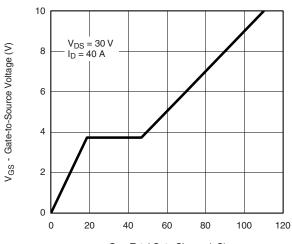
Capacitance



Transfer Characteristics



On-Resistance vs. Drain Current

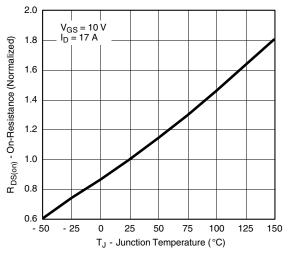


 $\mathbf{Q}_{\mathbf{g}}$ - Total Gate Charge (nC)

Gate Charge

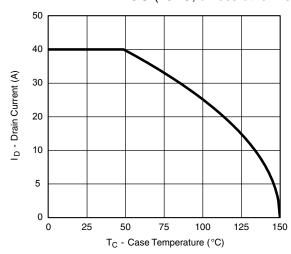


TYPICAL CHARACTERISTICS

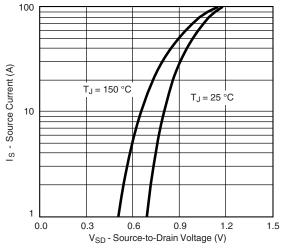


On-Resistance vs. Junction Temperature

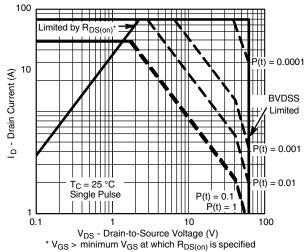
THERMAL RATINGS (25 °C, unless otherwise noted)



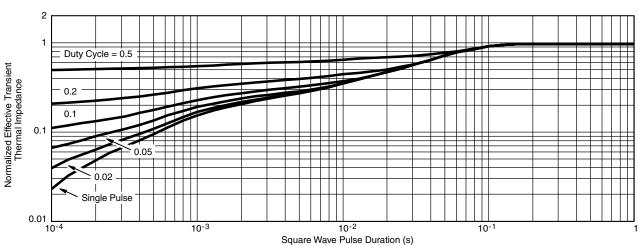
Drain Current vs. Case Temperature



Source-Drain Diode Forward Voltage



Safe Operating Area

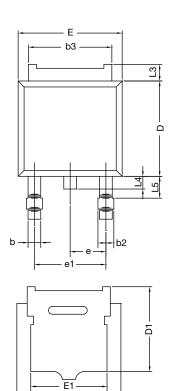


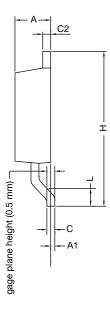
Normalized Thermal Transient Impedance, Junction-to-Case





TO-252AA CASE OUTLINE





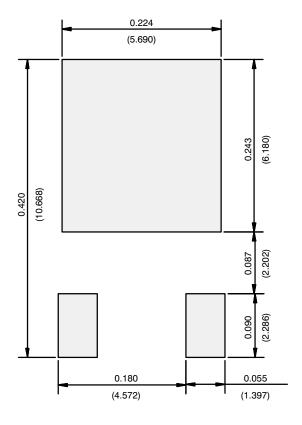
	MILLIN	METERS	INCHES		
DIM.	MIN.	MAX.	MIN.	MAX.	
Α	2.18	2.38	0.086	0.094	
A1	-	0.127	-	0.005	
b	0.64	0.88	0.025	0.035	
b2	0.76	1.14	0.030	0.045	
b3	4.95	5.46	0.195	0.215	
С	0.46	0.61	0.018	0.024	
C2	0.46	0.89	0.018	0.035	
D	5.97	6.22	0.235	0.245	
D1	5.21	-	0.205	-	
Е	6.35	6.73	0.250	0.265	
E1	4.32	-	0.170	-	
Н	9.40	10.41	0.370	0.410	
е	2.28	BSC	0.090 BSC		
e1	4.56 BSC		0.180 BSC		
L	1.40	1.78	0.055	0.070	
L3	0.89	1.27	0.035	0.050	
L4	-	1.02	-	0.040	
L5	1.14	1.52	0.045	0.060	
ECN: X12-0247-Rev. M, 24-Dec-12					

DWG: 5347 Note

• Dimension L3 is for reference only.



RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads Dimensions in Inches/(mm)

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